

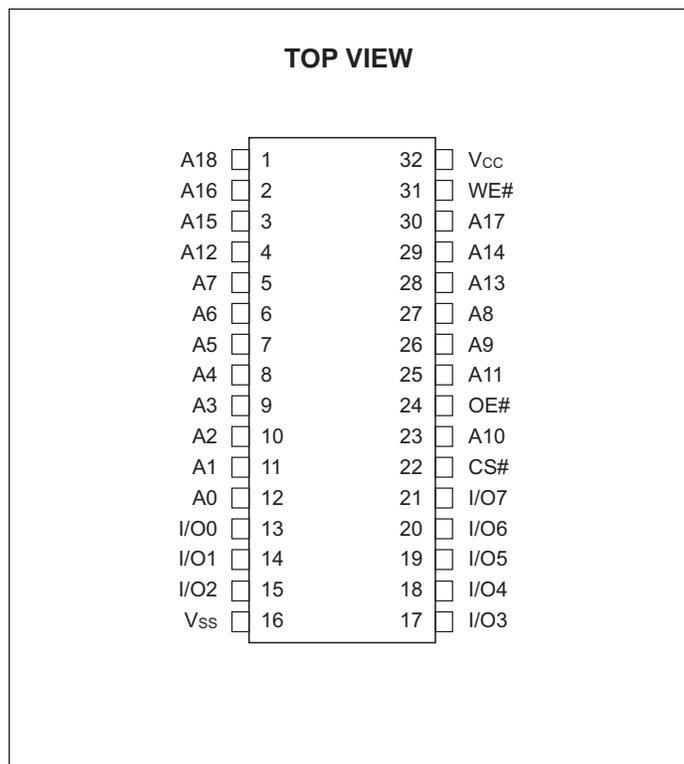
512Kx8 CMOS EEPROM, WE512K8-XCX, SMD 5962-93091

512Kx8 BIT CMOS EEPROM MODULE

FEATURES

- Read Access Times of 150, 200, 250, 300ns
- JEDEC Standard 32 Pin, Hermetic Ceramic DIP (Package 300)
- Commercial, Industrial and Military Temperature Ranges
- MIL-STD-883 Compliant Devices Available
- Write Endurance 10,000 Cycles
- Data Retention at 25°C, 10 Years
- Low Power CMOS Operation:
 - 3mA Standby Typical/100mA Operating Maximum
- Automatic Page Write Operation
 - Internal Address and Data Latches for
 - 512 Bytes, 1 to 128 Bytes/Row, Four Pages
- Page Write Cycle Time 10mS Max.
- Data Polling for End of Write Detection
- Hardware and Software Data Protection
- TTL Compatible Inputs and Outputs

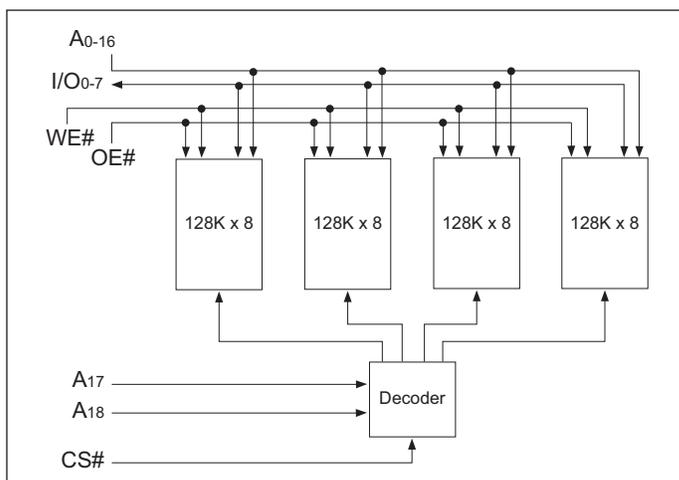
FIGURE 1 – PIN CONFIGURATION



PIN DESCRIPTION

A0-18	Address Inputs
I/O0-7	Data Input/Output
CS#	Chip Select
OE#	Output Enable
WE#	Write Enable
V _{CC}	+5.0V Power
V _{SS}	Ground

BLOCK DIAGRAM



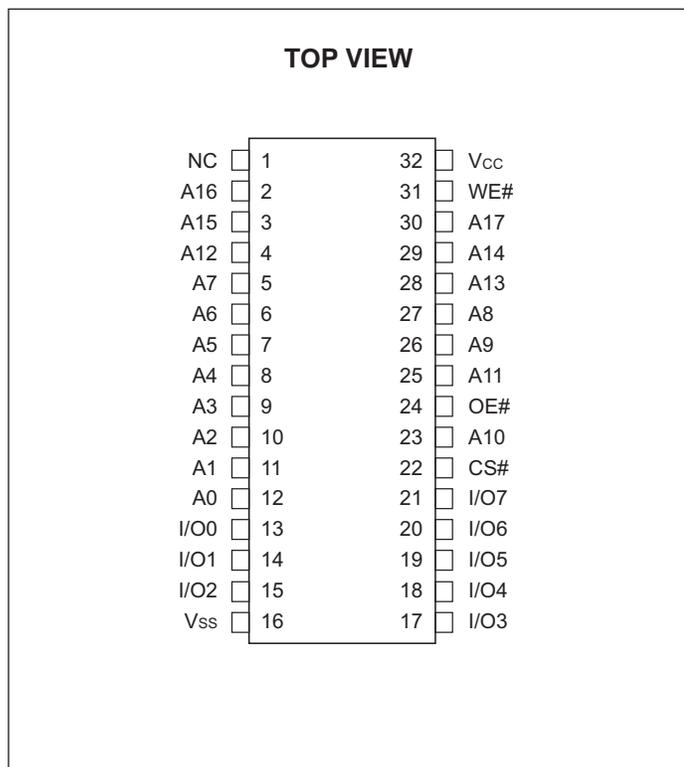
256Kx8 CMOS EEPROM, WE256K8-XCX, SMD 5962-93155

256KX8 BIT CMOS EEPROM MODULE

FEATURES

- Read Access Times of 150, 200ns
- JEDEC Standard 32 Pin, Hermetic Ceramic DIP (Package 302)
- Commercial, Industrial and Military Temperature Ranges
- MIL-STD-883 Compliant Devices Available
- Write Endurance 10,000 Cycles
- Data Retention at 25°C, 10 Years
- Low Power CMOS Operation:
 - 2mA Standby Typical/90mA Operating Maximum
- Automatic Page Write Operation
- Internal Address and Data Latches for
- 512 Bytes, 1 to 64 Bytes/Row, Eight Pages
- Page Write Cycle Time 10mS Max.
- Data Polling for End of Write Detection
- Hardware and Software Data Protection
- TTL Compatible Inputs and Outputs

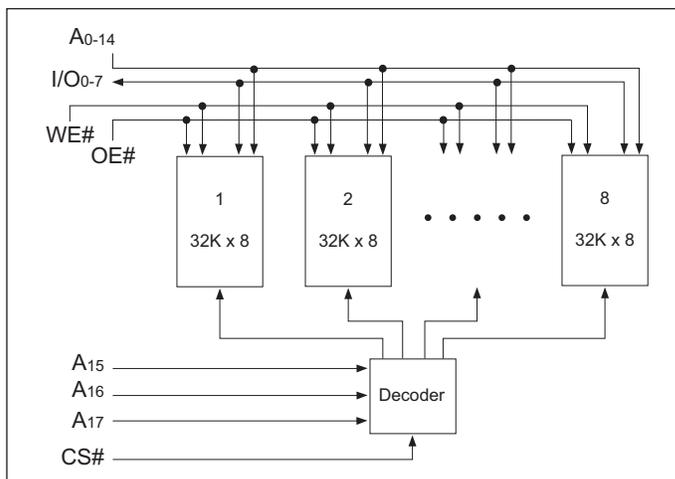
FIGURE 2 – PIN CONFIGURATION



PIN DESCRIPTION

A0-18	Address Inputs
I/O0-7	Data Input/Output
CS#	Chip Select
OE#	Output Enable
WE#	Write Enable
Vcc	+5.0V Power
Vss	Ground

BLOCK DIAGRAM



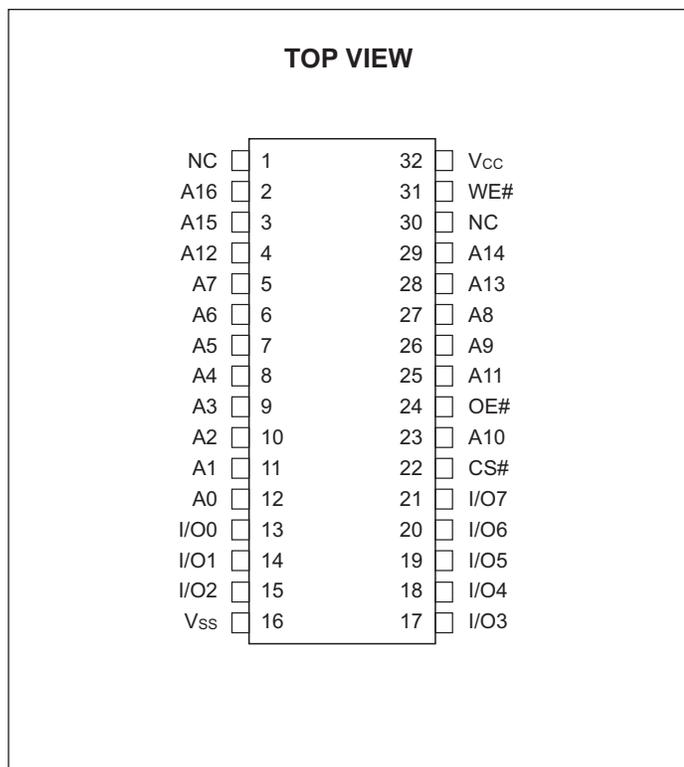
128Kx8 CMOS EEPROM, WE128K8-XCX, SMD 5962-93154

128Kx8 BIT CMOS EEPROM MODULE

FEATURES

- Read Access Times of 150, 200ns
- JEDEC Standard 32 Pin, Hermetic Ceramic DIP (Package 300)
- Commercial, Industrial and Military Temperature Ranges
- MIL-STD-883 Compliant Devices Available
- Write Endurance 10,000 Cycles
- Data Retention at 25°C, 10 Years
- Low Power CMOS Operation:
 - 1mA Standby Typical/70mA Operating
- Automatic Page Write Operation
 - Internal Address and Data Latches for
 - 256 Bytes, 1 to 64 Bytes/Row, Four Pages
- Page Write Cycle Time 10mS Max.
- Data Polling for End of Write Detection
- Hardware and Software Data Protection
- TTL Compatible Inputs and Outputs

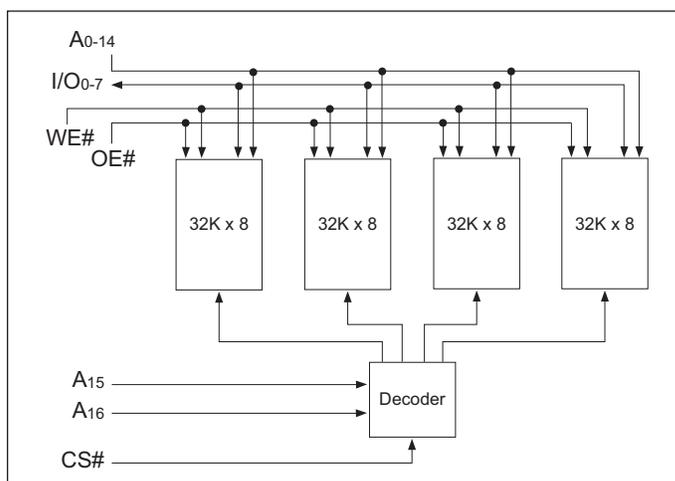
FIGURE 3 – PIN CONFIGURATION



PIN DESCRIPTION

A0-18	Address Inputs
I/O0-7	Data Input/Output
CS#	Chip Select
OE#	Output Enable
WE#	Write Enable
Vcc	+5.0V Power
Vss	Ground

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol		Unit
Operating Temperature	T _A	-55 to +125	°C
Storage Temperature	T _{STG}	-65 to +150	°C
Signal Voltage Any Pin	V _G	-0.6 to +6.25	V
Voltage on OE# and A9		-0.6 to +13.5	V
Thermal Resistance junction to case	θ _{JC}	28	°C/W
Lead Temperature (soldering -10 secs)		+300	°C

NOTE:

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V _{CC}	4.5	5.5	V
Input High Voltage	V _{IH}	2.0	V _{CC} + 0.3	V
Input Low Voltage	V _{IL}	-0.3	+0.8	V
Operating Temp. (Mil.)	T _A	-55	+125	°C
Operating Temp. (Ind.)	T _A	-40	+85	°C

TRUTH TABLE

CS#	OE#	WE#	Mode	Data I/O
H	X	X	Standby	High Z
L	L	H	Read	Data Out
L	H	L	Write	Data In
X	H	X	Out Disable	High Z/Data Out
X	X	H	Write	
X	L	X	Inhibit	

CAPACITANCE

T_A = +25°C

Parameter	Sym	Condition	512Kx8 Max	256Kx8 Max	128Kx8 Max	Unit
Input Capacitance	C _{IN}	V _{IN} = 0V, f = 1MHz	45	80	45	pF
Output Capacitance	C _{OUT}	V _{I/O} = 0V, f = 1MHz	60	80	60	pF

This parameter is guaranteed by design but not tested.

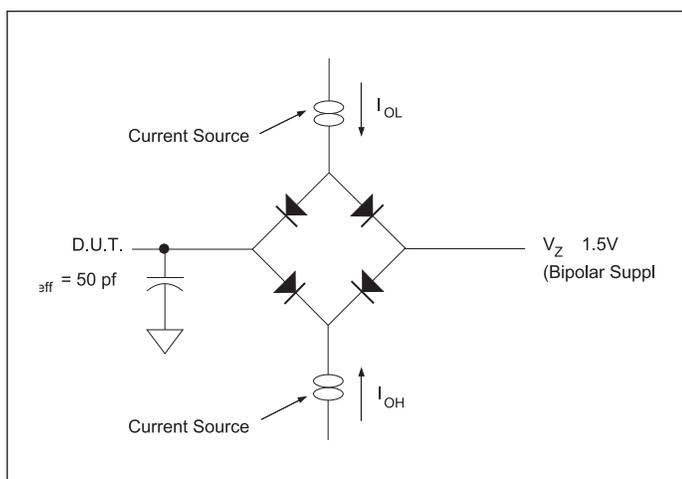
DC CHARACTERISTICS

V_{CC} = 5.0V, V_{SS} = 0V, -55°C ≤ T_A ≤ +125°C

Parameter	Symbol	Conditions	512K x 8			256K x 8			128K x 8			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
Input Leakage Current	I _{LI}	V _{CC} = 5.5, V _{IN} = GND to V _{CC}			10			10			10	µA
Output Leakage Current	I _{LO}	CS# = V _{IH} , OE# = V _{IH} , V _{out} = GND to V _{CC}			10			10			10	µA
Dynamic Supply Current	I _{CC}	CS# = V _{IL} , OE# = V _{IH} , f = 5MHz, V _{CC} = 5.5		80	100		60	90		50	90	mA
Standby Current	I _{SB}	CS# = V _{IH} , OE# = V _{IH} , f = 5MHz, V _{CC} = 5.5		3	8		2	6		1	4	mA
Output Low Voltage	V _{OL}	I _{OL} = 2.1mA, V _{CC} = 4.5V			0.45			0.45			0.45	V
Output High Voltage	V _{OH}	I _{OH} = -400µA, V _{CC} = 4.5V	2.4			2.4			2.4			V

NOTE: DC test conditions: V_{IH} = V_{CC} - 0.3V, V_{IL} = 0.3V

FIGURE 4 – AC TEST CIRCUIT



AC TEST CONDITIONS

Parameter	Typ	Unit
Input Pulse Levels	V _{IL} = 0, V _{IH} = 3.0	V
Input Rise and Fall	5	ns
Input and Output Reference Level	1.5	V
Output Timing Reference Level	1.5	V

Notes: V_Z is programmable from -2V to +7V.

I_{OL} & I_{OH} programmable from 0 to 16mA.

Tester Impedance Z₀ = 75Ω.

V_Z is typically the midpoint of V_{OH} and V_{OL}.

I_{OL} & I_{OH} are adjusted to simulate a typical resistive load circuit.

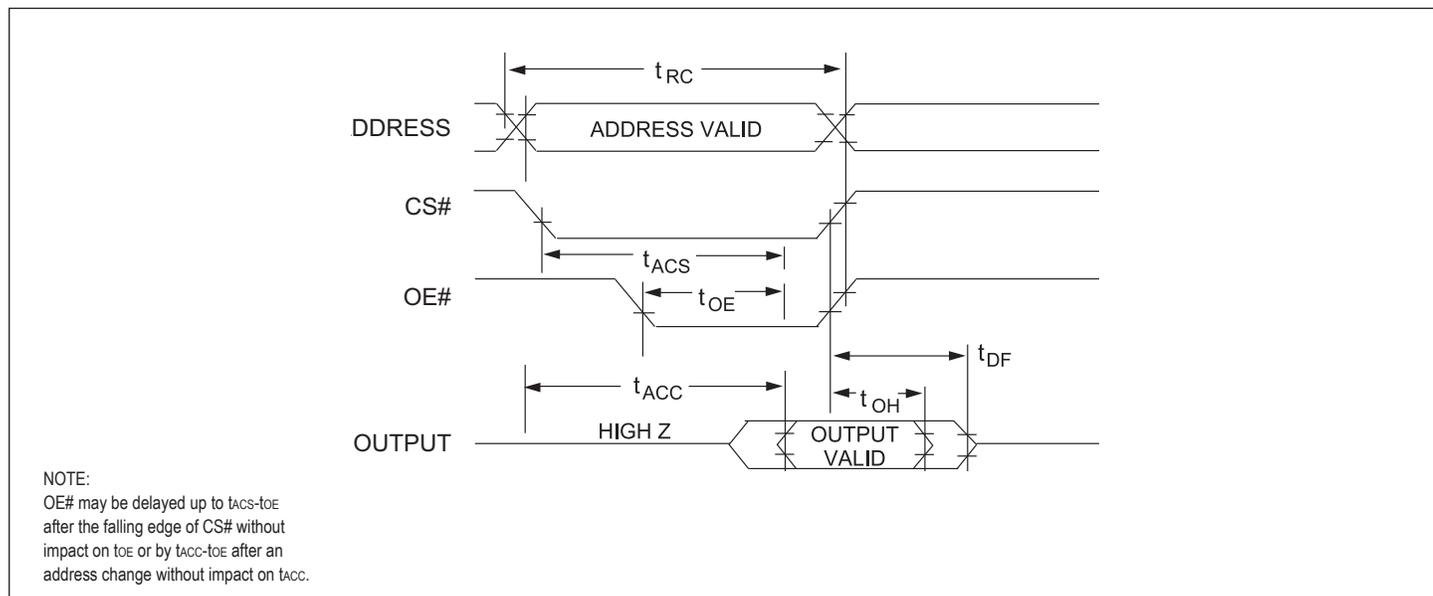
ATE tester includes jig capacitance.

READ

Figure 5 shows Read cycle waveforms. A read cycle begins with selection address, chip select and output enable. Chip select is accomplished by placing the CS# line low. Output enable is done by placing the OE# line low. The memory places the selected data

byte on I/O0 through I/O7 after the access time. The output of the memory is placed in a high impedance state shortly after either the OE# line or CS# line is returned to a high level.

FIGURE 5 – READ WAVEFORMS



AC READ CHARACTERISTICS (See Figure 5) FOR WE512K8-XCX

$V_{CC} = 5.0V, V_{SS} = 0V, -55^{\circ}C \leq T_A \leq +125^{\circ}C$

Parameter	Symbol	-150		-200		-250		-300		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
Read Cycle Time	trc	150		200		250		300		ns
Address Access Time	tacc		150		200		250		300	ns
Chip Select Access Time	tacs		150		200		250		300	ns
Output Hold from Address Change, OE# or CS#	toh	0		0		0		0		ns
Output Enable to Output Valid	toe		85		85		100		125	ns
Chip Select or Output Enable to High Z Output	tdf		70		70		70		70	ns

FOR WE256K8-XCX and WE128K8-XCX

Parameter	Symbol	-150		-200		Unit
		Min	Max	Min	Max	
Read Cycle Time	trc	150		200		ns
Address Access Time	tacc		150		200	ns
Chip Select Access Time	tacs		150		200	ns
Output Hold from Address Change, OE# or CS#	toh	0		0		ns
Output Enable to Output Valid	toe		85		85	ns
Chip Select or Output Enable to High Z Output	tdf		70		70	ns

WRITE

Write operations are initiated when both CS# and WE# are low and OE# is high. The EEPROM devices support both a CS# and WE# controlled write cycle. The address is latched by the falling edge of either CS# or WE#, whichever occurs last.

The data is latched internally by the rising edge of either CS# or WE#, whichever occurs first. A byte write operation will automatically continue to completion.

WRITE CYCLE TIMING

Figures 6 and 7 show the write cycle timing relationships. A write cycle begins with address application, write enable and chip select. Chip select is accomplished by placing the CS# line low. Write enable consists of setting the WE line low. The write cycle begins when the last of either CS# or WE# goes low.

The WE# line transition from high to low also initiates an internal 150µsec delay timer to permit page mode operation. Each subsequent WE# transition from high to low that occurs before the completion of the 150µsec time out will restart the timer from zero. The operation of the timer is the same as a retrigable one-shot.

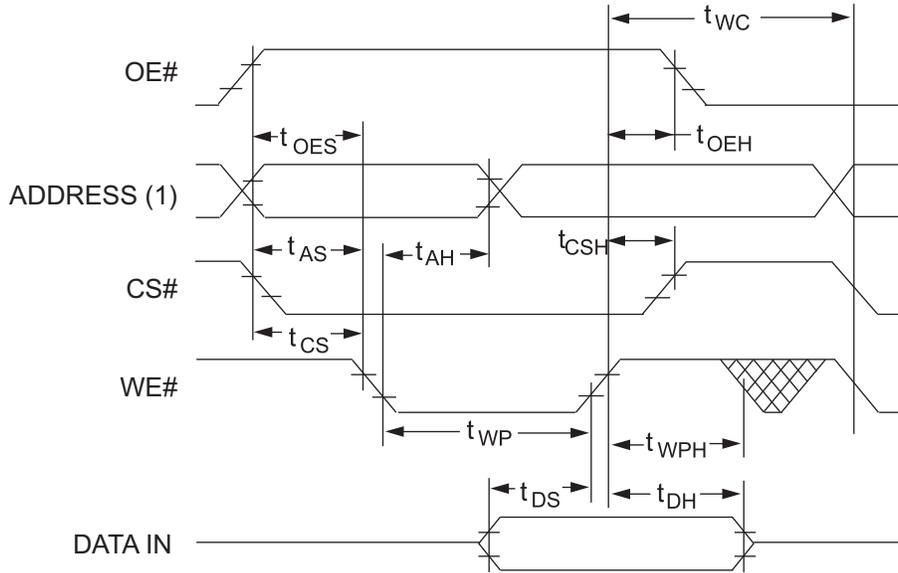
AC WRITE CHARACTERISTICS

$V_{CC} = 5.0V, V_{SS} = 0V, -55^{\circ}C \leq T_A \leq +125^{\circ}C$

Parameter	Symbol	512K x 8		256K x 8		128K x 8		Unit
		Min	Max	Min	Max	Min	Max	
Write Cycle Time, TYP = 6mS	t _{WC}		10		10		10	ms
Address Set-up Time	t _{AS}	10		30		30		ns
Write Pulse Width (WE# or CS#)	t _{WP}	150		150		150		ns
Chip Select Set-up Time	t _{CS}	0		0		0		ns
Address Hold Time (1)	t _{AH}	125		50		50		ns
Data Hold Time	t _{DH}	10		0		0		ns
Chip Select Hold Time	t _{CH}	0		0		0		ns
Data Set-up Time	t _{DS}	100		100		100		ns
Output Enable Set-up Time	t _{OES}	10		30		30		ns
Output Enable Hold Time	t _{OEH}	10		0		0		ns
Write Pulse Width High	t _{WPH}	50		50		50		ns

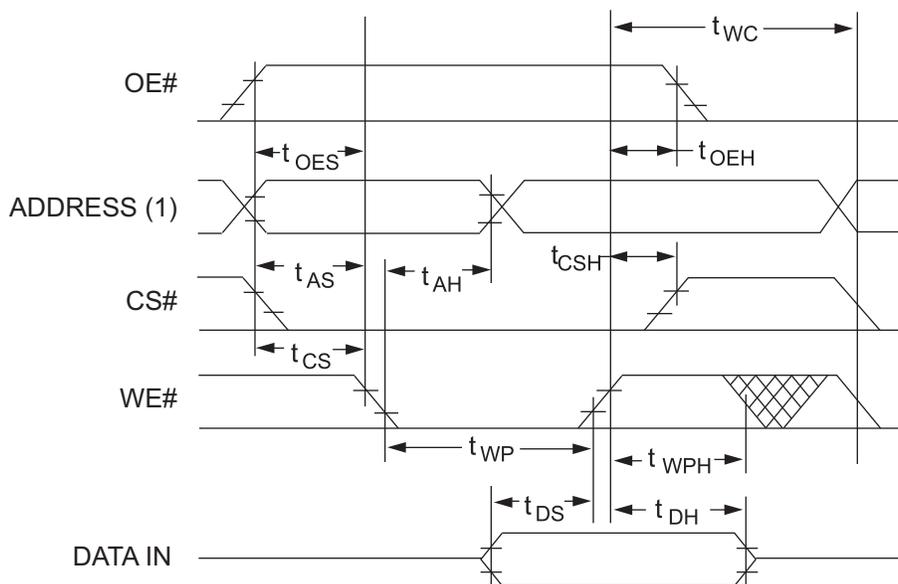
NOTES:

1. A17 and A18 must remain valid through WE# and CS# low pulse, for 512K x 8.
 A15, A16, and A17 must remain valid through WE# and CS# low pulse, for 256K x 8.
 A15 and A16 must remain valid through WE# and CS# low pulse, for 128K x 8.

FIGURE 6 – WRITE WAVEFORMS WE# CONTROLLED


NOTE:

1. Decoded Address Lines must be valid for the duration of the write.

FIGURE 7 – WRITE WAVEFORMS CS# CONTROLLED


NOTE:

1. Decoded Address Lines must be valid for the duration of the write.

DATA POLLING

Operation with data polling permits a faster method of writing to the EEPROM. The actual time to complete the memory programming cycle is faster than the guaranteed maximum.

The EEPROM features a method to determine when the internal programming cycle is completed. After a write cycle is initiated, the EEPROM will respond to read cycles to provide the microprocessor with the status of the programming cycle. The status consists of the last data byte written being returned with data bit I/O₇ complemented during the programming cycle, and I/O₇ true after completion.

Data polling allows a simple bit test operation to determine the status of the EEPROM. During the internal programming cycle, a read of the last byte written will produce the complement of the data on I/O₇. For example, if the data written consisted of I/O₇ = HIGH, then the data read back would consist of I/O₇ = LOW.

A polled byte write sequence would consist of the following steps:

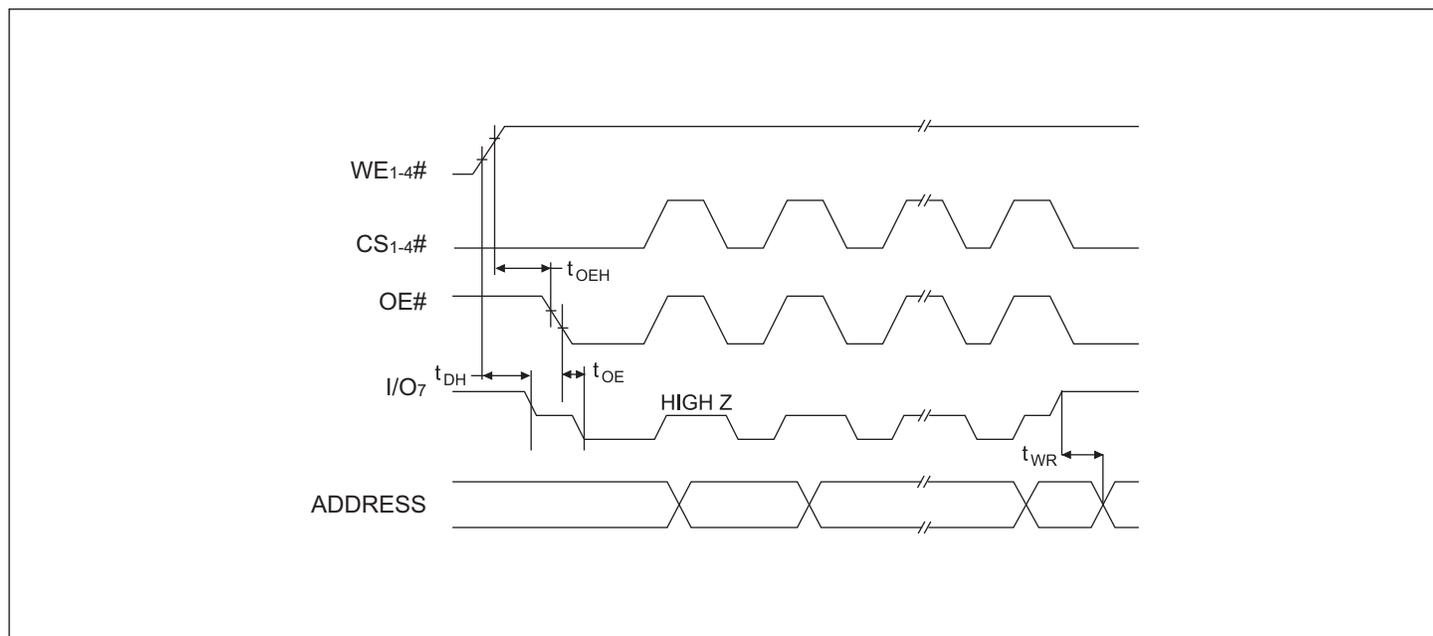
1. write byte to EEPROM
2. store last byte and last address written
3. release a time slice to other tasks
4. read byte from EEPROM - last address
5. compare I/O₇ to stored value
 - a) If different, write cycle is not completed, go to step 3.
 - b) If same, write cycle is completed, go to step 1 or step 3.

DATA POLLING AC CHARACTERISTICS

$V_{CC} = 5.0V, V_{SS} = 0V, -55^{\circ}C \leq T_A \leq +125^{\circ}C$

Parameter	Symbol	512Kx8		256Kx8		128Kx8		Unit
		Min	Max	Min	Max	Min	Max	
Data Hold Time	t_{DH}	10		0		0		ns
Output Enable Hold Time	t_{OEh}	10		0		0		ns
Output Enable To Output Delay	t_{OE}		100		100		100	ns
Write Recovery Time	t_{WR}	0		0		0		ns

FIGURE 8 – DATA POLLING WAVEFORMS



PAGE WRITE OPERATION

These devices have a page write operation that allows one to 64 bytes of data (one to 128 bytes for the WE512K8) to be written into the device and then simultaneously written during the internal programming period. Successive bytes may be loaded in the same manner after the first data byte has been loaded. An internal timer begins a time out operation at each write cycle. If another write cycle is completed within 150 μ s or less, a new time out period begins. Each write cycle restarts the delay period. The write cycles can be continued as long as the interval is less than the time out period.

The usual procedure is to increment the least significant address lines from A₀ through A₅ (A₀ through A₆ for the WE512K8) at each write cycle. In this manner a page of up to 64 bytes (128 bytes for the WE512K8) can be loaded into the EEPROM in a burst mode before beginning the relatively long interval programming cycle.

After the 150 μ s time out is completed, the EEPROM begins an internal write cycle. During this cycle the entire page of bytes will be written at the same time. The internal programming cycle is the same regardless of the number of bytes accessed.

The page address must be the same for each byte load and must be valid during each high to low transition of WE# (or CS#). The block address also must be the same for each byte load and must remain valid throughout the WE# (or CS#) low pulse. The page and block address lines are summarized below:

PAGE MODE CHARACTERISTICS

V_{CC} = 5.0V, V_{SS} = 0V, -55°C ≤ T_A ≤ +125°C

Parameter	Symbol	Min	Max	Unit
Write Cycle Time, TYP = 6mS	t _{WC}		10	ms
Data Set-up Time	t _{DS}	100		ns
Data Hold Time	t _{DH}	10		ns
Write Pulse Width	t _{WP}	150		ns
Byte Load Cycle Time	t _{BLC}		150	μ s
Write Pulse Width High	t _{WPH}	50		ns

Device	Block Address	Page Address
WE512K8-XCX	A17-A18	A7-A16
WE256K8-XCX	A15-A17	A6-A14
WE128K8-XCX	A15-A16	A6-A14

FIGURE 9 – PAGE WRITE WAVEFORMS

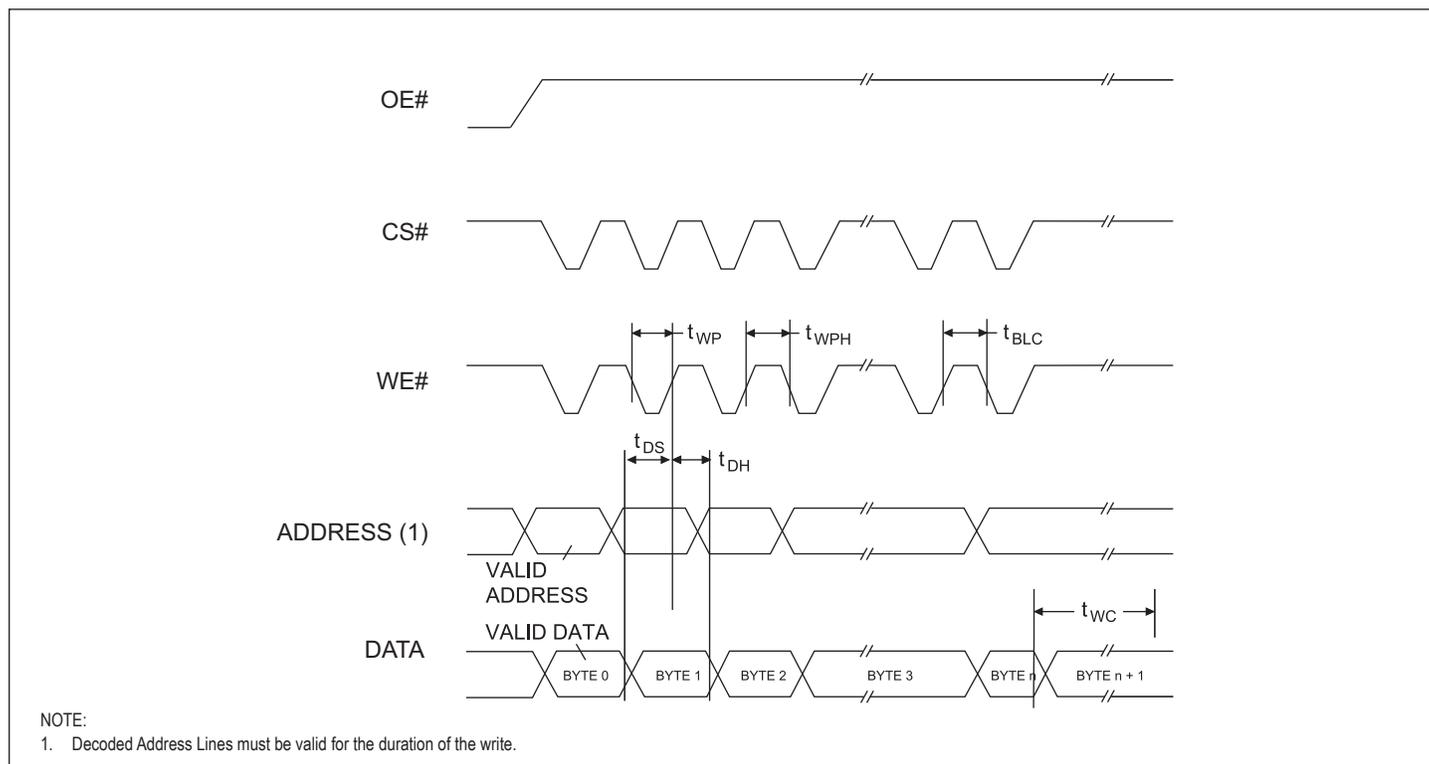
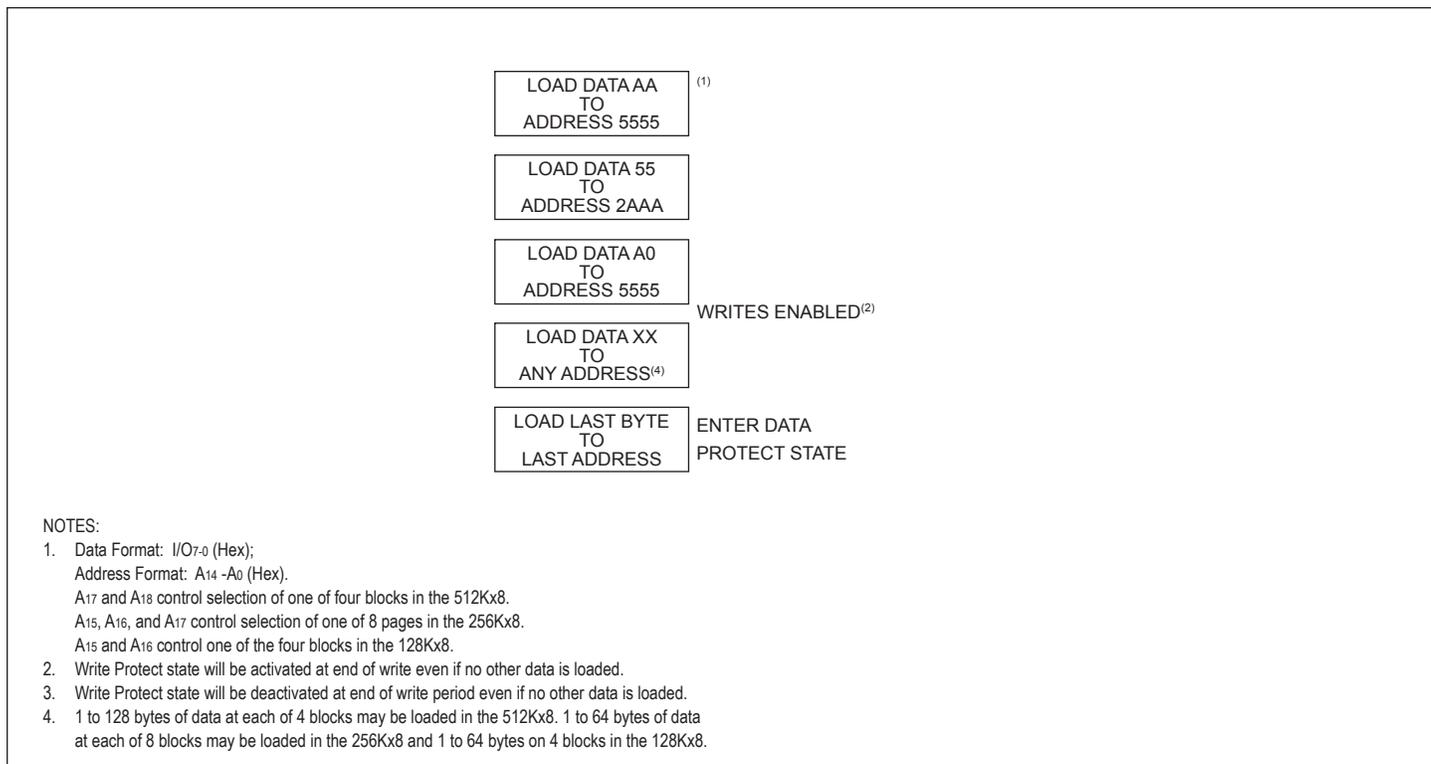
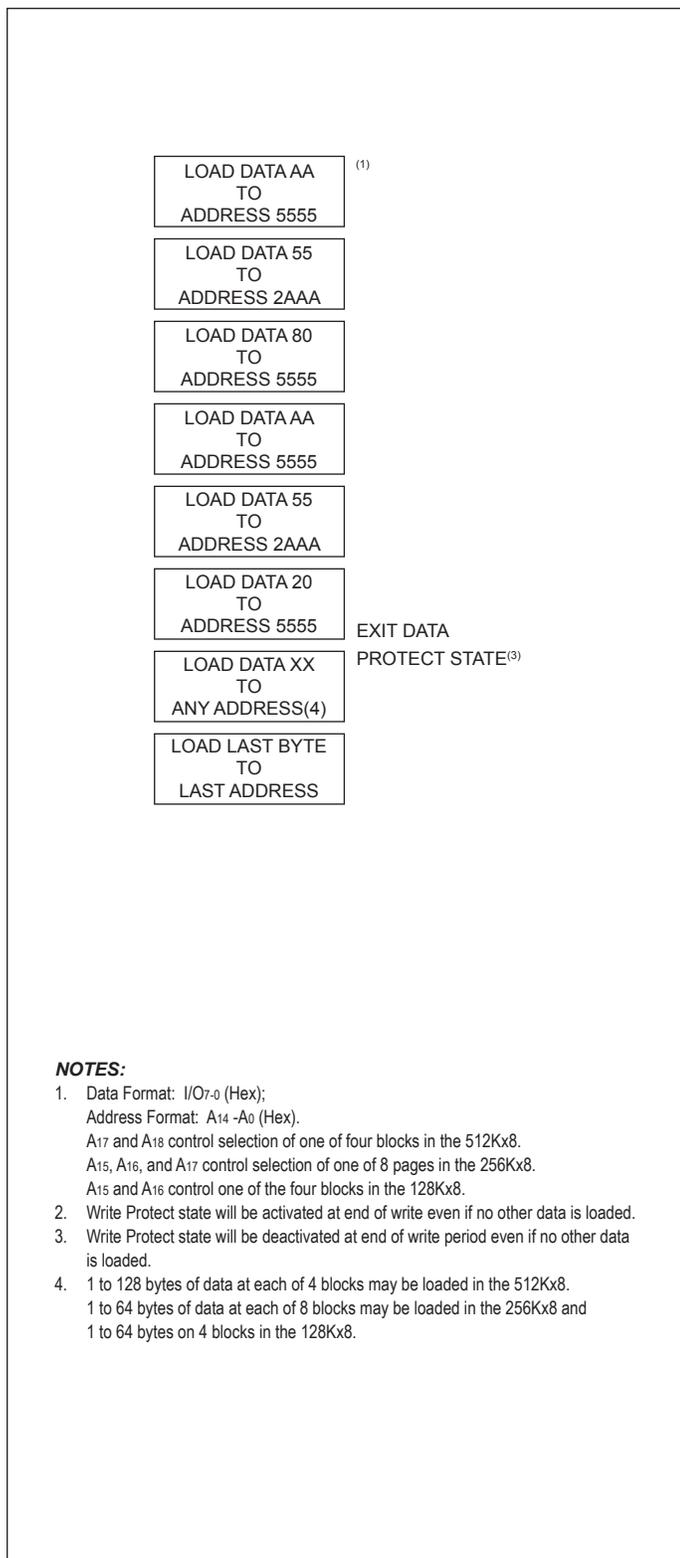


FIGURE 10 – SOFTWARE BLOCK DATA PROTECTION ENABLE ALGORITHM


**FIGURE 11 –
 SOFTWARE BLOCK DATA
 PROTECTION DISABLE ALGORITHM**



SOFTWARE DATA PROTECTION

A software write protection feature may be enabled or disabled by the user. When shipped by White Microelectronics, the devices have the feature disabled. Write access to the device is unrestricted.

To enable software write protection, the user writes three access code bytes to three special internal locations. Once write protection has been enabled, each write to the EEPROM must use the same three byte write sequence to permit writing. After setting software data protection, any attempt to write to the device without the three-byte command sequence will start the internal write timers. No data will be written to the device, however, for the duration of *t_{wc}*. The write protection feature can be disabled by a six byte write sequence of specific data to specific locations. Power transitions will not reset the software write protection.

Each 32K byte block (128K bytes for the WE512K8) of EEPROM has independent write protection. One or more blocks may be enabled and the rest disabled in any combination. The software write protection guards against inadvertent writes during power transitions or unauthorized modification using a PROM programmer. The block selection is controlled by the upper most address lines (A17 through A18 for the WE512K8, A15 through A17 for the WE256K8, or A15 and A16 for the WE128K8).

HARDWARE DATA PROTECTION

Several methods of hardware data protection have been implemented in the White Microelectronics EEPROM. These are included to improve reliability during normal operations.

a) V_{cc} power on delay

As V_{cc} climbs past 3.8V typical the device will wait 5mSec typical before allowing write cycles.

b) V_{cc} sense

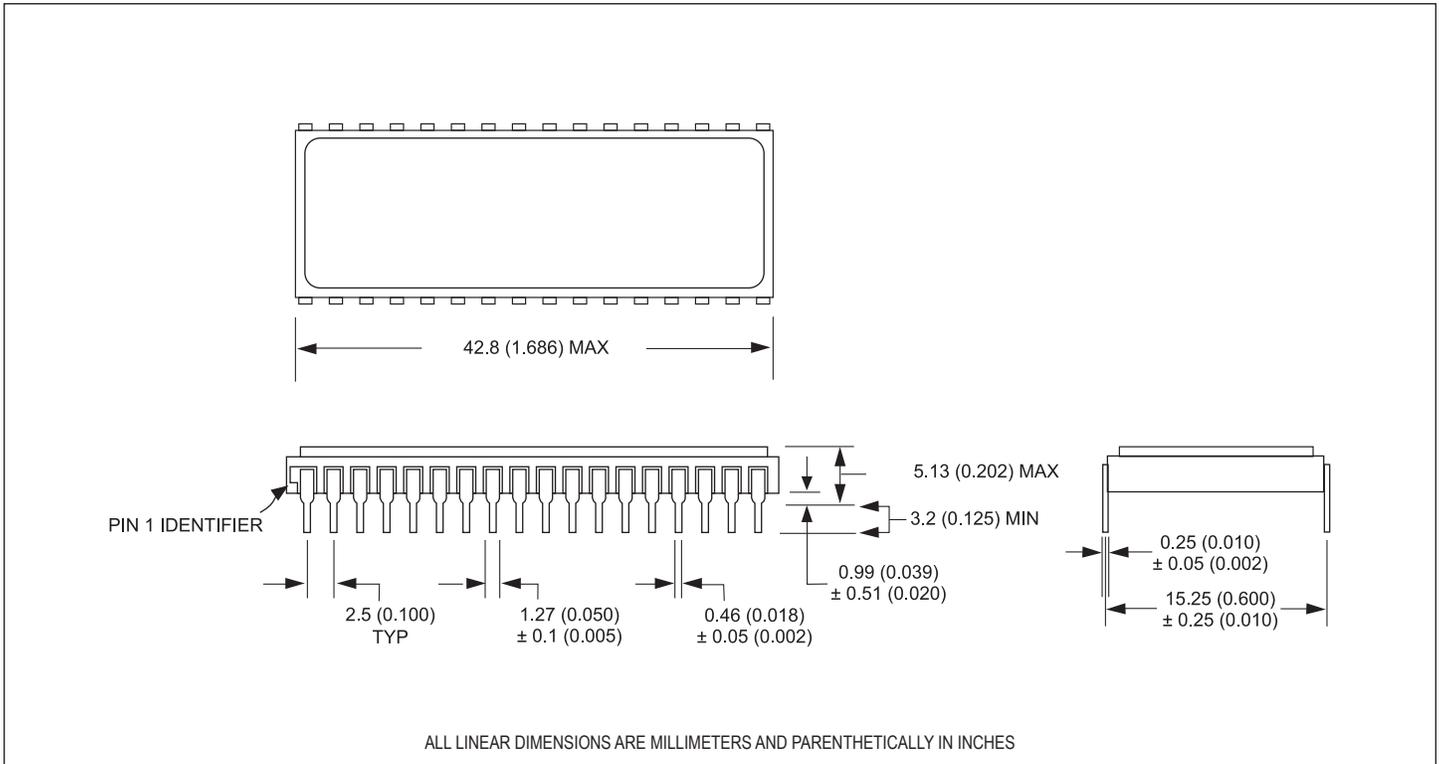
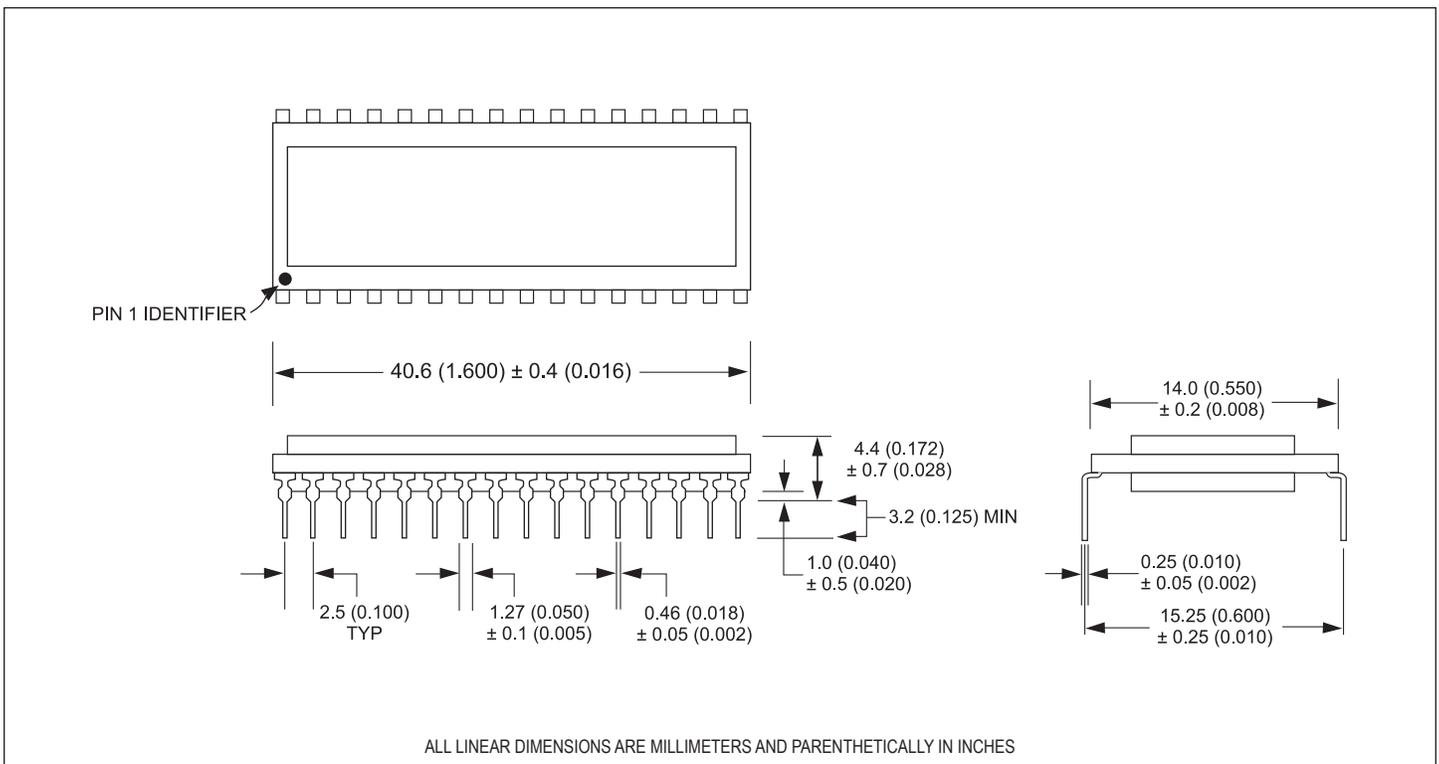
While below 3.8V typical write cycles are inhibited.

c) Write inhibiting

Holding OE# low and either CS# or WE# high inhibits write cycles.

d) Noise filter

Pulses of <8ns (typ) on WE# or CS# will not initiate a write cycle.

PACKAGE 300 – 32 PIN, CERAMIC DIP, SINGLE CAVITY SIDE BRAZED

PACKAGE 302 – 32 PIN, CERAMIC DIP, DUAL CAVITY BOTTOM BRAZED


ORDERING INFORMATION

	W E XXXK8 - XXX C X X
MICROSEMI CORPORATION _____	
EEPROM _____	
Organization, 512Kx8, 256Kx8 or 128Kx8 _____	
ACCESS TIME (ns) _____	
PACKAGE: _____	
C = Ceramic DIP (Package 300 for 128Kx8) (Package 302 for 256Kx8) (Package 300 for 512Kx8)	
PROCESSING: _____	
Q = MIL-STD-883 Compliant M = Military Screened -55°C to +125°C I = Industrial -40°C to +85°C C = Commercial 0°C to +70°C	
LEAD FINISH: _____	
Blank = Gold plated leads A = Solder dip leads	

Device Type	Speed	Package	WM Part No.	SMD No.
512K x 8 EEPROM	150ns	32 pin DIP (C)	WE512K8-150CQ	5962-93091 01HYX
512K x 8 EEPROM	300ns	32 pin DIP (C)	WE512K8-300CQ	5962-93091 02HYX
512K x 8 EEPROM	250ns	32 pin DIP (C)	WE512K8-250CQ	5962-93091 03HYX
512K x 8 EEPROM	200ns	32 pin DIP (C)	WE512K8-200CQ	5962-93091 04HYX
256K x 8 EEPROM	200ns	32 pin DIP (C)	WE256K8-200CQ	5962-93155 01HYX
256K x 8 EEPROM	150ns	32 pin DIP (C)	WE256K8-150CQ	5962-93155 02HYX
128K x 8 EEPROM	200ns	32 pin DIP (C)	WE128K8-200CQ	5962-93154 01HXX
128K x 8 EEPROM	150ns	32 pin DIP (C)	WE128K8-150CQ	5962-93154 02HXX



Document Title

512Kx8 CMOS EEPROM, WE512K8-XCX, SMD 5962-93091

Revision History

Rev #	History	Release Date	Status
Rev 4	Changes (Pg. 1-14) 4.1 Change document layout from White Electronic Designs to Microsemi 4.2 Add document Revision History page	August 2011	Final